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covering one of the at least two magneto resistive elements to prevent additional removal of material from the covered magneto resistive element in response to the monitoring step.

3. (Amended) The method of claim 22 wherein the dynamically covering step takes place when the electrical resistance meets a selected level.

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4. (Amended) The method of claim 21 wherein the placing step includes placing the at least two magneto resistive elements in an ion milling environment.

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6. (Amended) The method of claim 22 wherein the step of dynamically covering one of the at least two of the magneto resistive elements further comprises actuating a shutter to substantially cover one of the at least two magneto resistive elements.

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8. (Amended) An apparatus for use in a wafer process comprising:

a carrier;

an elongated element held by the carrier; and

a mask including a first shutter, a second shutter, and an actuator for moving the first shutter and second shutter, wherein said mask is used to selectively cover a first portion of the elongated element as the wafer process continues to act on a second portion of the elongated element, the wafer process substantially halting with respect to the first portion of the elongated element.

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9. The apparatus of claim 8 wherein the [dynamic] mask is a dynamic mask.

17. (Amended) The apparatus of claim 13 wherein the electrical resistance is measured during the wafer process of ion milling.

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18. (Amended) The apparatus of claim 17 wherein the electrical resistance is measured during the wafer process of ion milling and wherein the controller moves at least one of the first shutter and the second shutter over at least one of the magneto resistive elements during the process of ion milling, wherein the shutter has a width to substantially protect the magneto resistive element below the shutter from removal of material when the shutter is placed in a covering position over the magneto resistive element.

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19. (Amended) The apparatus of claim 12, wherein a magneto resistive element selected from the plurality of magneto resistive elements includes a stripe having a stripe height, the resistance measured across the magneto resistive element is related to the stripe height.

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21. (New) The method of claim 1 wherein the placing step includes nonselectively removing material from items in the environment.

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22. (New) The method of claim 1 wherein the covering step further includes dynamically covering.

23. (New) A method for producing magneto resistive heads comprising the steps of:

positioning at least two magneto resistive elements in spaced relation to one another;

placing the at least two magneto resistive elements in an environment

removing material from items in the environment;

monitoring a property of the at least two magneto resistive elements; and

covering one of the at least two magneto resistive elements by actuating a shutter to substantially cover one of the at least two magneto resistive elements to prevent additional removal of material during the monitoring step.

24. (New) The method of claim 23 wherein the monitoring step further comprises the steps of:

electrically connecting the at least two magneto resistive elements; and

measuring the electrical resistance of the at least two magneto resistive elements.

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25. (New) The method of claim 23 wherein the covering step further includes dynamically covering.

26. (New) The method of claim 25 wherein the dynamically covering step takes place when the electrical resistance meets a selected level.

27. (New) The method of claim 25 wherein the step of dynamically covering one of the at least two of the magneto resistive elements further comprises actuating a shutter to substantially cover the at least two magneto resistive elements.

28. (New) The method of claim 23 wherein the removing step includes nonselectively removing material from items in the environment.

29. (New) The method of claim 23 wherein the placing step includes placing the at least two magneto resistive elements in an ion milling environment.

30. (New) An apparatus for use in a wafer process comprising:

a carrier;

an elongated element held by the carrier; and

a mask including at least one shutter and an actuator for moving the at least one shutter, wherein said mask is used to selectively cover a first portion of the elongated element as the wafer process continues to act on a second portion of the elongated element, the wafer process substantially halting with respect to the first portion of the elongated element.

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31. (New) The apparatus of claim 30 wherein the mask is a dynamic mask.

32. (New) The apparatus of claim 31 further comprising a controller for the actuator, the controller actuating the at least one shutter between an open position where the at least one shutter is not covering a portion of the elongated element and a covering position where the at least one shutter is covering a portion of the elongated element.

33. (New) The apparatus of claim 31 further comprising:

a controller for the actuator, the controller actuating the at least one shutter between an open position where the at least one shutter is not covering a portion of the elongated element and a covering position where the at least one shutter is covering a portion of the elongated element; and

a mechanism for measuring a property associated with a selected portion of the elongated element, wherein the controller actuates the at least one shutter in response to a selected value of a measured property.

34. (New) The apparatus of claim 33, wherein the elongated element is a rowbar containing a plurality of magneto resistive elements.

35. (New) The apparatus of claim 34, wherein at least one magneto resistive element of the plurality of magneto resistive elements is monitored for electrical resistance, the

apparatus further comprising a controller for the actuator, the controller actuating the at least one shutter between an open position where the at least one shutter is not covering a portion of the elongated element, and a covering position where the at least one shutter is covering a portion of the elongated element, in response to the electrical resistance associated with that portion of the elongated element being at a predefined value.

36. (New) The apparatus of claim 35, wherein the electrical resistance is measured during the wafer process of ion milling.

37. (New) The apparatus of claim 36, wherein the electrical resistance is measured during the wafer process of ion milling and wherein the controller moves the at least one shutter over the at least one magneto resistive element during the process of ion milling, wherein the at least one shutter has a width to substantially protect the magneto resistive below the at least one shutter from removal of material where the shutter is placed in a covering position of the at least magneto resistive element.

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38. (New) The apparatus of claim 34, wherein at least one magneto resistive element selected from the plurality of magneto resistive elements includes a stripe having a stripe height, the resistance measured across the at least one magneto resistive element is related to the strip height.

39. (New) An apparatus for use in a wafer process comprising:

a carrier;

an elongated element held by the carrier;

a mask including at least one shutter and an actuator for moving the at least one shutter, wherein said mask is used to selectively cover a first portion of the elongated element as the wafer process continues to act on a second portion of the elongated element, the wafer process substantially halting with respect to the first portion of the elongated element; and

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a controller for the actuator, the controller actuating the at least one shutter between an open position where the at least one shutter is not covering a portion of the elongated element, and a covering position where the at least one shutter is covering the portion of the elongated element, in response to a monitored property level associated with the portion of the elongated element being at a predefined value.